ELSEVIER

Journal of Crystal Growth 160 (1996) 414–417

JOURNAL OF CRYSTAL GROWTH

Author index

Adachi, S., see Suto 160 (1996) 13
Ahmed, M.U., E.D. Jones and N.M. Stewart, Cd self-diffusion in Cu doped CdTe 160 (1996) 36
Alexiev, D., see Mo 160 (1996) 7
Aoyagi, Y., see Lee 160 (1996) 21
Atanassova, S., K. Neykov and I. Gutzow, Solubility, inhibited growth and dissolution kinetics of calcium oxalate crystals in solutions, containing α-ketoglutaric acid 160 (1996) 148

Barata, P.A. and M.L. Serrano, Salting-out precipitation of potassium dihydrogen phosphate (KDP). I. Precipitation mechanism 160 (1996) 361
Barber, P.G., A.L. Fripp, Jr., W.J. Debnam, Jr., G. Woodell, R.F. Berry and R.T. Simchick, Experimental verification of agreement between thermal and real time visual melt–solid interface positions in vertical Bridgman grown germanium 160 (1996) 55
Barnes, J.E. and K.P. Trumble, Tri-arc Czochralski growth of single crystal molybdenum disilicide 160 (1996) 66
Berry, R.F., see Barber 160 (1996) 55
Bertru, N., M. Nouaoura, J. Bonnet and L. Lassabatere, GaSb molecular beam epitaxy growth on vicinal surfaces studied by RHEED 160 (1996) 1
Bhat, H.L., see Dutta 160 (1996) 177
Bhat, H.L., see Dutta 160 (1996) 207
Billia, B., Report on the book "Shaped Crystal Growth" by V.A. Tatarchenko [Kluwer, Dordrecht, The Netherlands – ISBN 0-7923-2419-6] 160 (1996) 413
Bonnet, J., see Bertru 160 (1996) 1
Bottomley, D.J. and P. Fons, The strain energy density of cubic epitaxial layers 160 (1996) 406
Bravi, M., see Söhnel 160 (1996) 355
Buchanan, M., see Finnie 160 (1996) 220
Bulutcu, A.N., see Yuksel 160 (1996) 370
Butcher, K.S.A., see Mo 160 (1996) 7
Butcher, K.S.A., see Zhou 160 (1996) 201

Chen, J.F., see Wang 160 (1996) 241
Chen, W.K., see Wang 160 (1996) 241
Chianese, A., see Söhnel 160 (1996) 355
Choi, D.Y., see Jung 160 (1996) 305
Chong, T.C., see Zeng 160 (1996) 289
Chong, T.C., see Zeng 160 (1996) 296
Chung, S.-I., see Togawa 160 (1996) 41
Chung, S-I., see Togawa 160 (1996) 49
Chung, S.J., see Jung 160 (1996) 305
Cookson, D.J., see Gerson 160 (1996) 346
Counter, J.A., see Gerson 160 (1996) 346

Debnam Jr., W.J., see Barber 160 (1996) 55
Diéguez, E., see Dutta 160 (1996) 177
Diéguez, E., see Dutta 160 (1996) 207
Diéguez, E., see Santos 160 (1996) 283
Dutta, P.S., H.L. Bhat, V. Kumar, N.V. Sochinskii and E. Diéguez, Influence of arsenic concentration on the surface morphology and photoluminescence of LPE grown AlGaAsSb/GaSb with high aluminium content 160 (1996) 177
Dutta, P.S., C. Marín, E. Diéguez and H.L. Bhat, Compositional mapping of GaSb wafers from as-grown crystals and after post-growth annealing treatments 160 (1996) 207

Eckler, K., see Li 160 (1996) 59
Evans, A., see Riley 160 (1996) 193
Ewing, F.L., E.L. Forsythe, M. van der Woerd and M.L. Pusey, Effects of purification on the crystallization of lysozyme 160 (1996) 389

Finnie, P., M. Buchanan, C. Lacelle and A.P. Roth, Growth of quantum wire structures by selective area chemical beam epitaxy 160 (1996) 220
Fons, P., see Bottomley 160 (1996) 406
Forsythe, E.L., see Ewing 160 (1996) 389
Foulon, M., see Van Miltenburg 160 (1996) 141
Fripp Jr., A.L., see Barber 160 (1996) 55
Fukuda, A., see Yamada 160 (1996) 279
Fukuda, T., see Kochurikhin 160 (1996) 181
Fukui, T., see Ohkuri 160 (1996) 235

Gallagher, H.G., see Qi 160 (1996) 111
Gerson, A.R., J.A. Counter and D.J. Cookson, Influence of solution constituents, solution conditioning and seeding on the crystalline

phase of aluminium hydroxide using in situ X-ray diffraction 160 (1996) 346
Goiffon, A., see Philippot 160 (1996) 268
Gonda, T. and H. Nakahara, Formation mechanism of side branches of dendritic ice crystals grown from vapor 160 (1996) 162
Gutzow, I., see Atanassova 160 (1996) 148

Hahn, J.H., see Hwang 160 (1996) 87
Han, T.P.J., see Qi 160 (1996) 111
Hara, S., see Ikemiya 160 (1996) 104
Hara, S., see Ohkuri 160 (1996) 235
Henderson, B., see Qi 160 (1996) 111
Herlach, D.M., see Li 160 (1996) 59
Hicks, R.F., see Kappers 160 (1996) 310
Hirano, M., see Zeng 160 (1996) 289
Hirano, M., see Zeng 160 (1996) 296
Hoshi, H., see Yamada 160 (1996) 279
Hu, W.R., see Wang 160 (1996) 398
Hwang, N.M., J.H. Hahn and D.Y. Yoon, Chemical potential of carbon in the low pressure synthesis of diamond 160 (1996) 87
Hwang, N.M. and D.Y. Yoon, Thermodynamic approach to the paradox of diamond formation with simultaneous graphite etching in the low pressure synthesis of diamond 160 (1996) 98

Ibanez, A., see Philippot 160 (1996) 268
Ikemiya, N., A. Kitamura and S. Hara, Surface structures of MgO(100) and $SrTiO_3$(100) as revealed by atomic force microscopy 160 (1996) 104
Illingworth, R., see Qi 160 (1996) 111
Ishikawa, K., see Yamada 160 (1996) 279
Ishizaki, J., see Ohkuri 160 (1996) 235
Isshiki, H., see Lee 160 (1996) 21
Iwai, S., see Lee 160 (1996) 21
Izunome, K., see Togawa 160 (1996) 41
Izunome, K., see Togawa 160 (1996) 49

Jayaraman, D., see Kumar 160 (1996) 129
Jiang Yandao, see Zheng Hong 160 (1996) 136
Jones, E.D., see Ahmed 160 (1996) 36
Josiek, A. and F. Langlais, Residence-time dependent kinetics of CVD growth of SiC in the MTS/H_2 system 160 (1996) 253
Josiek, A., Nonstoichiometry and nanocrystallization of silicon-rich silicon carbide deposited by chemical vapor deposition 160 (1996) 261
Ju, Yulin, see Li 160 (1996) 250
Jung, S.T., D.Y. Choi and S.J. Chung, Crystal growth of $NdAl_3(BO_3)_4$ from $K_2O/MoO_3/Nd_2O_3/B_2O_3$/KF flux 160 (1996) 305

Kagi, H., see Li 160 (1996) 78
Kanai, H., M. Kimura, A. Tanaka and T. Sukegawa, LPE growth of GaAs by yo-yo solute feeding method 160 (1996) 229
Kappers, M.J., A.H. McDaniel and R.F. Hicks, Controlling the group II composition in CdZnTe alloys grown by organometallic vapor phase epitaxy: a kinetic model 160 (1996) 310
Kawanishi, S., see Togawa 160 (1996) 41
Kawanishi, S., see Togawa 160 (1996) 49
Kimura, M., see Kanai 160 (1996) 229
Kimura, S., see Togawa 160 (1996) 41
Kimura, S., see Togawa 160 (1996) 49
Kipp, S. and R. Lacmann, Cooling crystallization experiments observed by in situ scanning force microscopy 160 (1996) 320
Kitamura, A., see Ikemiya 160 (1996) 104
Kochurikhin, V.V., K. Shimamura and T. Fukuda, Investigation of spiral bending of straight Czochralski grown dysprosium gallium aluminium garnet crystals 160 (1996) 181
Krukowski, S. and J.C. Tedenac, Fractal to compact transition during growth of 2D Kossel crystal in vapor diffusion field 160 (1996) 167
Kumagai, H., see Zeng 160 (1996) 289
Kumagai, H., see Zeng 160 (1996) 296
Kumar, F.J., S.G. Moorthy, D. Jayaraman and C. Subramanian, Estimation of metastable zone width, interfacial energy and growth rates of $KTiOPO_4$ crystallizing from $K_6P_4O_{13}$ flux by hot stage microscopy 160 (1996) 129
Kumar, V., see Dutta 160 (1996) 177

Lacelle, C., see Finnie 160 (1996) 220
Lacmann, R., see Kipp 160 (1996) 320
Langlais, F., see Josiek 160 (1996) 253
Lassabatere, L., see Bertru 160 (1996) 1
Laügt, S., see Massies 160 (1996) 211
Lebrun, N., see Van Miltenburg 160 (1996) 141
Lee, J.-S., S. Iwai, H. Isshiki, T. Meguro, T. Sugano and Y. Aoyagi, Atomic layer epitaxy of GaAs and $GaAs_xP_{1-x}$ on nominally oriented GaAs(111) substrates with high quality surface and interfaces 160 (1996) 21
Leroux, M., see Massies 160 (1996) 211
Li, D., K. Eckler and D.M. Herlach, Development of grain structures in highly undercooled germanium and copper 160 (1996) 59
Li, W., H. Kagi and M. Wakatsuki, A two-stage method for growing large single crystals of diamond with high quality 160 (1996) 78
Li, X., see Zhou 160 (1996) 201
Li, Yangxian, Yulin Ju, Caichi Liu, Yuesheng Xu and Hongmei Wang, Inhibition of neutron irradiation on oxidation stacking faults on the surface of Si wafers 160 (1996) 250
Lim, L.C., see Zeng 160 (1996) 289
Lim, L.C., see Zeng 160 (1996) 296
Liu, Caichi, see Li 160 (1996) 250

Marín, C., see Dutta 160 (1996) 207
Marín, C., see Santos 160 (1996) 283

Markman, O., C. Roh, M.F. Roberts and M.M. Teeter, Designed additives for controlled growth of crystals of phospholipid interacting proteins: Short chain phospholipids 160 (1996) 382
Martinez, Y., see Massies 160 (1996) 211
Massies, J., M. Leroux, Y. Martinez, P. Vennegues and S. Laügt, Molecular beam epitaxy of GaSb/$Al_xGa_{1-x}Sb$ quantum well structures 160 (1996) 211
Matsushita, H. and T. Takizawa, Single crystal growth of $CuInSe_2$ by selenization horizontal Bridgman method 160 (1996) 71
Mazzarotta, B., see Söhnel 160 (1996) 355
McDaniel, A.H., see Kappers 160 (1996) 310
Meekes, H., see Verheijen 160 (1996) 337
Meguro, T., see Lee 160 (1996) 21
Mo, L., K.S.A. Butcher and D. Alexiev, Effect of crucible materials on impurities in LPE-GaAs 160 (1996) 7
Moorthy, S.G., see Kumar 160 (1996) 129

Nakahara, H., see Gonda 160 (1996) 162
Neykov, K., see Atanassova 160 (1996) 148
Nishizawa, J., see Suto 160 (1996) 13
Nouaoura, M., see Bertru 160 (1996) 1

Ohkuri, K., J. Ishizaki, S. Hara and T. Fukui, Multiatomic step formation on GaAs(001) vicinal surfaces during thermal treatment 160 (1996) 235

Philippot, E., A. Goiffon and A. Ibanez, Comparative crystal habit study of quartz and MPO_4 isomorphous compounds (M = Al,Ga) 160 (1996) 268
Polak, W. and K. Sangwal, Theoretical estimation of solvation parameters and interfacial tension of clusters of potassium halides in aqueous solutions 160 (1996) 154
Pusey, M.L., see Ewing 160 (1996) 389

Qi, X., R. Illingworth, H.G. Gallagher, T.P.J. Han and B. Henderson, Potential laser gain media with the stoichiometric formula RE-$TiNbO_6$ 160 (1996) 111

Riley, J., D. Wolfframm, D. Westwood and A. Evans, Studies in the growth of ZnSe on GaAs(001) 160 (1996) 193
Ristic, R.I., B. Shekunov and J.N. Shewood, Long and short period growth rate variations in potash alum crystals 160 (1996) 330
Roberts, M.F., see Markman 160 (1996) 382
Roh, C., see Markman 160 (1996) 382
Roth, A.P., see Finnie 160 (1996) 220

Saiki, A., see Yamada 160 (1996) 279
Sangwal, K., see Polak 160 (1996) 154
Santos, M.T., C. Marín and E. Diéguez, Morphology of $Bi_{12}GeO_{20}$ crystals grown along the ⟨111⟩ directions by the Czochralski method 160 (1996) 283
Sasaki, A., Initial growth layers and critical thickness of InAs heteroepitaxy on GaAs substrates 160 (1996) 27
Sayan, P., see Yuksel 160 (1996) 370
Serrano, M.L., see Barata 160 (1996) 361
Shekunov, B., see Ristic 160 (1996) 330
Shewood, J.N., see Ristic 160 (1996) 330
Shi Erwei, see Wang Buguo 160 (1996) 375
Shih, C.-Y., see Tai 160 (1996) 186
Shimamura, K., see Kochurikhin 160 (1996) 181
Simchick, R.T., see Barber 160 (1996) 55
Sochinskii, N.V., see Dutta 160 (1996) 177
Söhnel, O., M. Bravi, A. Chianese and B. Mazzarotta, Growth kinetics of sodium perborate from batch crystallization 160 (1996) 355
Stewart, N.M., see Ahmed 160 (1996) 36
Strunk, H.P., Edge dislocations may cause growth spirals 160 (1996) 184
Subramanian, C., see Kumar 160 (1996) 129
Sugano, T., see Lee 160 (1996) 21
Sukegawa, T., see Kanai 160 (1996) 229
Suto, K., S. Adachi, T. Yoneyama and J. Nishizawa, Free exciton recombination in GaP and GaP/$Al_xGa_{1-x}P$ layers grown by temperature difference method under controlled vapor pressure 160 (1996) 13

Tai, C.Y. and C.-Y. Shih, A new model relating secondary nucleation rate and supersaturation 160 (1996) 186
Takezoe, H., see Yamada 160 (1996) 279
Takizawa, T., see Matsushita 160 (1996) 71
Tanaka, A., see Kanai 160 (1996) 229
Tansley, T.L., see Zhou 160 (1996) 201
Tedenac, J.C., see Krukowski 160 (1996) 167
Teeter, M.M., see Markman 160 (1996) 382
Terashima, K., see Togawa 160 (1996) 41
Terashima, K., see Togawa 160 (1996) 49
Titiz, S., see Yuksel 160 (1996) 370
Togawa, S., S.-I. Chung, S. Kawanishi, K. Izunome, K. Terashima and S. Kimura, Density anomaly effect upon silicon melt flow during Czochralski crystal growth. I. Under the growth interface 160 (1996) 41
Togawa, S., S-I. Chung, S. Kawanishi, K. Izunome, K. Terashima and S. Kimura, Density anomaly effect upon silicon melt flow during Czochralski crystal growth. II. Time-topical flow structure under the growth interface 160 (1996) 49
Trumble, K.P., see Barnes 160 (1996) 66

Van der Eerden, J.P., see Van Miltenburg 160 (1996) 141
Van der Woerd, M., see Ewing 160 (1996) 389

Van Miltenburg, J.C., N. Lebrun, J.P. van der Eerden and M. Foulon, Crystallization of methylhydrazine monohydrate under adiabatic conditions 160 (1996) 141
Vennegues, P., see Massies 160 (1996) 211
Verheijen, M.A., L.J.P. Vogels and H. Meekes, On the hypomorphism of ADP crystals 160 (1996) 337
Vogels, L.J.P., see Verheijen 160 (1996) 337

Wakatsuki, M., see Li 160 (1996) 78
Wang, Hongmei, see Li 160 (1996) 250
Wang, P.-Y., J.F. Chen and W.K. Chen, Structural and electrical properties of GaSb, AlGaSb and their heterostructures grown on GaAs by metalorganic chemical vapor deposition 160 (1996) 241
Wang, W. and W.R. Hu, Concentration distribution in crystallization from solution under microgravity 160 (1996) 398
Wang Buguo, Zhong Weizhuo, Ye Cheng, Shi Erwei and Yin Zhiwen, Analysis of growth habits of polar organic crystal N-4-nitrophenyl-(L)-prolinol (NPP) based on the incorporation of growth units 160 (1996) 375
Westwood, D., see Riley 160 (1996) 193
Wolfframm, D., see Riley 160 (1996) 193
Woodell, G., see Barber 160 (1996) 55
Wu Xing, see Zheng Hong 160 (1996) 136

Xia Hongchang, see Zheng Hong 160 (1996) 136
Xu, Yuesheng, see Li 160 (1996) 250

Yamada, K., H. Hoshi, K. Ishikawa, H. Takezoe, A. Fukuda and A. Saiki, Thick single crystalline vanadyl phthalocyanine film epitaxially grown on KBr crystal by molecular beam epitaxy 160 (1996) 279
Yang Huaguang, see Zheng Hong 160 (1996) 136
Ye Cheng, see Wang Buguo 160 (1996) 375
Yin Zhiwen, see Wang Buguo 160 (1996) 375
Yoneyama, T., see Suto 160 (1996) 13
Yoon, D.Y., see Hwang 160 (1996) 87
Yoon, D.Y., see Hwang 160 (1996) 98
Yuksel, G.Y., P. Sayan, S. Titiz and A.N. Bulutcu, Effect of silica on the crystallization of sodium perborate tetrahydrate 160 (1996) 370

Zeng, H.C., Rectangular vacancy island formation and self-depletion in Czochralski-grown $PbMoO_4$ single crystal during heat treatment 160 (1996) 119
Zeng, H.C., T.C. Chong, L.C. Lim, H. Kumagai and M. Hirano, Effects of meniscus on the directional growth of potassium niobate single crystals 160 (1996) 289
Zeng, H.C., T.C. Chong, L.C. Lim, H. Kumagai and M. Hirano, Two-level growth of potassium niobate $KNbO_3$ single crystals: a new growth method for ABO_3-type materials 160 (1996) 296
Zhang Yunzhi, see Zheng Hong 160 (1996) 136
Zheng Hong, Yang Huaguang, Zhang Yunzhi, Zhou Jianfei, Xia Hongchang, Wu Xing and Jiang Yandao, Nd:YVO_4 crystal growth by the floating zone method 160 (1996) 136
Zhong Weizhuo, see Wang Buguo 160 (1996) 375
Zhou, B., X. Li, T.L. Tansley and K.S.A. Butcher, Growth mechanisms in excimer laser photolytic deposition of gallium nitride at 500°C 160 (1996) 201
Zhou Jianfei, see Zheng Hong 160 (1996) 136

ELSEVIER

Journal of Crystal Growth 160 (1996) 418–419

JOURNAL OF CRYSTAL GROWTH

Subject index

Aluminum
- gallium arsenide antimonide 177
- hydroxide 346

Apparatus
- for diamond growth 78
- - of sodium perborate 355
- for miscellaneous purposes
- - in situ X-ray diffraction monitoring of solution growth 346

Cadmium
- telluride 36
- zinc telluride 310

Computer simulation
- of fractal to compact transition 167
- of thermal field 49

Convection 41, 49, 229

Copper
- indium selenide 71

Defects
- in ice crystals 162
- stacking faults in silicon 250

Dendritic growth
- of copper 59
- of germanium 59
- theory of fractal to compact transition 167

Device characterization
- deep levels in gallium arsenide 7
- quantum wells 211
- quantum wires and dots 220

Diamond 78, 87, 98

Diffusional control
- of cadmium in cadmium telluride 78

Dissolution
- of K alum 320
- of renal stones 148

Epitaxy, see Thin film growth

Gallium
- aluminum antimonide 241
- aluminum arsenide 235
- antimonide 1, 207, 241
- arsenide 7, 220, 229, 235
- arsenide phosphide 21
- indium arsenide 220
- nitride 201
- phosphide 13

Germanium 55

Hydrodynamics, see Convection

Ice 162

Indium
- arsenide 27

Kinetics
- of alloy composition 310
- of diffusion 1
- of dissolution 148
- of growth 21, 59, 78, 87, 98, 119, 129, 141, 184, 193, 229, 250, 253, 268, 310, 330, 355, 370
- of nucleation 87, 129, 186, 361, 370
- of thermal treatment 235
- of vacancy formation 119

Lasers, crystals for
- neodymium yttrium vanadate 136
- rare earth titanium niobate 111

Lysozyme 389

Melt growth technique
- by Bridgman–Stockbarger method
- - of copper indium selenide in horizontal configuration 71
- - of germanium 55
- by Czochralski method
- - of bismuth germanate 283
- - of dysprosium gallium aluminum garnet 181
- - of lead molybdate 119
- - of molybdenum disilicide 66
- - of silicon 41, 49
- by floating zone method
- - of neodymium yttrium vanadate 136
- by laser heated pedestal 111
- theory of nucleation 141

Microgravity, growth under
- of sodium chlorate 389
- theory of convection 398

Morphological stability
– of crystal facets 268, 375
– of ice crystals 162

Nucleation
– of aluminum hydroxide 346
– of diamond 87, 98
– of potassium dihydrogen phosphate 361
– of potassium halides 154
Numbers
– Rayleigh 41, 49

Phase diagram
– of methyl hydrazine water 141
Purification of materials
– of lysozyme 389

Quantum wells, see Device characterization
Quantum wires and dots, see Device characterization

Silicon 41, 250
– carbide 253, 261
Solution growth technique
– by additives
– – of protein crystals 382
– by continuous crystallization
– – of sodium perborate tetrahydrate 370
– by controlled slow cooling
– – of potash alum 330
– by flux method
– – of diamond 78
– – of neodymium aluminum borate 305
– – of sodium niobate 289
– – of sodium titanium monoxidephosphate 129
– by hydrothermal growth
– – of aluminum phosphate 268
– – of gallium phosphate 268
– by low temperature method
– – of N-4-nitrophenyl(L) prolinol (NPP) 375
– – theory of cluster formation 154
– by two level flux method
– – of sodium niobate 296
– by undercooling 320
Surface energy, determination
– of ionic clusters 154
– of sodium titaniummonoxide phosphate 129
Surface structure
– of aluminum gallium arsenide antimonide 177
– of ammonium dihydrogen phosphate 337
– of crystals 268
– of gallium antimonide 207
– of magnesium oxide 104
– of strontium titanate 104
– of thermal treated surfaces 235

Thin film growth, epitaxy 184
– by atomic layer epitaxy
– – of gallium arsenide 21
– – of gallium arsenide phosphide 21
– by liquid phase epitaxy
– – of aluminum gallium arsenide antimonide 177
– – of gallium aluminum phosphide 13
– – of gallium arsenide 7, 229
– by molecular beam epitaxy
– – of aluminum gallium antimonide 211
– – of gallium antimonide 1, 211
– – of gallium arsenide 220
– – of gallium indium arsenide 220
– – of indium arsenide 27
– – of vanadyl phthalocyanine 279
– – of zinc selenide 193
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of diamond 87, 98
– – – of silicon carbide 253, 261
– – – theory of simultaneous etching and growth 98
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium antimonide 241
– – – of cadmium zinc telluride 310
– – – of gallium antimonide 241
– – – of gallium nitride 201
– – theory of nanocrystallization 261
– theory of strain energy density of cubic epilayers 406

Zinc
– selenide 193